

4N2X Series 4N3X Series H11AX Series

Features:

- 4N2X series: 4N25, 4N26, 4N27, 4N28
- 4N3X series: 4N35, 4N36, 4N37, 4N38
- H11AX series: H11A1, H11A2, H11A3, H11A4, H11A5
- High isolation voltage between input and output (Viso=5000 V rms)
- Creepage distance >7.62 mm
- Operating temperature up to +110°C
- Compact dual-in-line package
- Pb free and RoHS compliant.
- UL approved (No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approval
- DEMKO approval
- FIMKO approval
- CSA approved
- CQC approved

Description

The 4N2X, 4N3X, H11AX series of devices each consist of an infrared emitting diode optically coupled to a phototransistor.

They are packaged in a 6-pin DIP package and available in wide-lead spacing and SMD option.

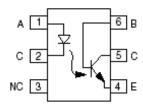
1

Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs



Schematic



- 1. Anode
- 2. Cathode
- 3. No Connection
- 4. Emitter
- 5. Collector
- 6. Base



4N2X Series 4N3X Series H11AX Series

Absolute Maximum Ratings (T_a=25°C)

	Parameter	Symbol	Rating	Unit
	Forward current	l _F	60	mA
	Peak forward current (t = 10µs)	I _{FM}	1	Α
Input	Reverse voltage	V_{R}	6	V
	Power dissipation (T _A = 25°C)		100	mW
	Derating factor (above 100°C)	P_{D}	3.8	mW/°C
	Collector-Emitter voltage	V _{CEO}	80	V
	Collector-Base voltage	V _{CBO}	80	V
Output	Emitter-Collector voltage	V _{ECO}	3.8 80 80 7	V
	Emitter-Base voltage	V _{EBO}	7	V
	Power dissipation (T _A = 25°C)		150	mW
	Derating factor (above 100°C)	P _C	9.0	mW/°C
Total power diss	sipation	P _{tot}	200	mW
Isolation voltage *1		V _{iso}	5000	Vrms
Operating temperature		T _{opr}	-55~+110	°C
Storage temperature		T _{stg}	-55~+125	°C
Soldering temperature *2		T _{sol}	260	°C

Notes

^{*1} AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 & 3 are shorted together, and pins 4, 5 & 6 are shorted together.

^{*2} For 10 seconds.



4N2X Series 4N3X Series H11AX Series

Electrical Characteristics (T_a=25°C unless specified otherwise)

Input

Parameter	Symbol	Min.	Тур.*	Max.	Unit	Condition
Forward voltage	V _F	1	1.2	1.5	V	I _F = 10mA
Reverse current	I _R	-	-	10	μA	V _R = 6V
Input capacitance	C _{in}	-	30	-	pF	V = 0, f = 1MHz

Output

Parameter		Symbol	Min.	Typ.*	Max.	Unit	Condition	
Collector-Base dark current		I _{CBO}	-	-	20	nA	V _{CB} = 10V	
Collector-Emitter dark current	4N2X H11AX	I _{CEO}	-	-	50	nA	nA	V _{CE} = 10V, IF=0mA
	4N3X		-	-	50		V _{CE} = 60V, IF=0mA	
Collector-Emitter breakdown voltage		BV _{CEO}	80	-	-	V	I _c =1mA	
Collector-Base breakdown voltage		BV _{CBO}	80	-	-	V	I _C =0.1mA	
Emitter-Collector breakdown voltage		BV _{ECO}	7	-	-	V	I _E =0.1mA	
Emitter-Base breakdown voltage		BV _{EBO}	7	-	-	V	I _E =0.1mA	
Collector-Emitter capacitance		C _{CE}	-	8	-	pF	VCE=0V, f=1MHz	

^{*} Typical values at T_a = 25°C



4N2X Series 4N3X Series H11AX Series

Transfer Characteristics (T_a=25°C unless specified otherwise)

Parameter		Symbol	Min.	Тур.*	Max.	Unit	Condition
	4N35, 4N36, 4N37		100	-	-	%	
	H11A1		50	-	-		
Current	H11A5	CTR	30	-	-		
transfer ratio	4N25, 4N26, 4N38, H11A2, H11A3		20	-	-		I _F = 10mA, V _{CE} = 10V
	4N27, 4N28, H11A4		10	-	-		
	4N25, 4N26, 4N27, 4N28		-	-	0.5		I _F = 50mA, I _c = 2mA
Collector-Emitter	4N35, 4N36, 4N37	V _{CE(sat)}	-	-	0.3	V	
saturation voltage	H11A1, H11A2, H11A3, H11A4, H11A5		-	-	0.4		I _F = 10mA, I _c = 0.5mA
	4N38		-	-	1.0		I _F = 20mA, I _c = 4mA
Isolation resistance	ce	R _{IO}	10 ¹¹	_	-	Ω	V _{IO} = 500Vdc
Input-output capa	citance	C _{IO}	-	0.2	-	pF	V _{IO} = 0, f = 1MHz
Turn-on time	4N25, 4N26, 4N27, 4N28, H11A1, H11A2, H11A3, H11A4, H11A5	Ton	ı	3	10	μs	V_{CC} = 10V, I_F = 10mA, R_L = 100 Ω See Fig. 11
	4N35, 4N36, 4N37, 4N38		-	10	12		$V_{CC} = 10V, I_{C} = 2mA,$ $R_{L} = 100\Omega, See Fig. 11$
Turn-off time	4N25, 4N26, 4N27, 4N28, H11A1, H11A2, H11A3, H11A4	Toff	-	3	10	μs	V_{CC} = 10V, I_F = 10mA, R_L = 100 Ω See Fig. 11
	4N35, 4N36, 4N37, 4N38		-	9	12		V_{CC} = 10V, I_C = 2mA, R_L = 100 Ω , See Fig. 11



Typical Performance Curves

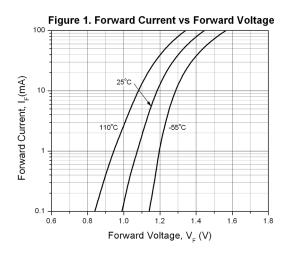


Figure 3. Current Tranfer Ratio vs Ambient Temperature

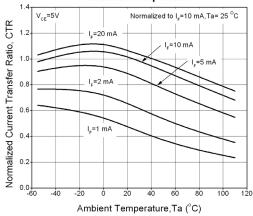


Figure 5. Current Transfer Ratio (Unsaturated) vs Base-Emitter Resistance

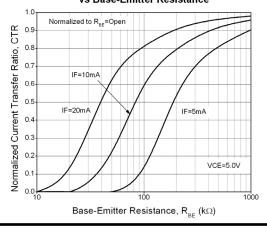


Figure 2. Current Tranfer Ratio vs Forward Current

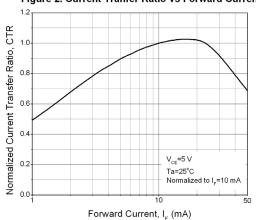


Figure 4. Current Transfer Ratio (Saturated)

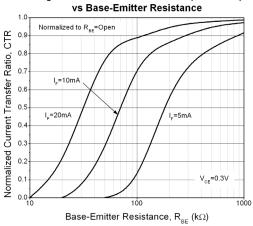
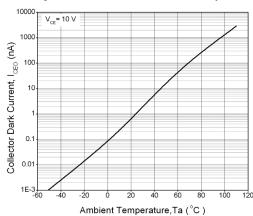


Figure 6. Dark Current vs Ambient Temperature





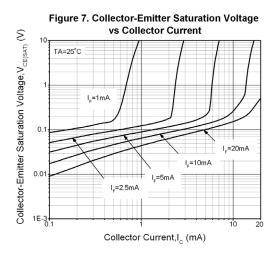
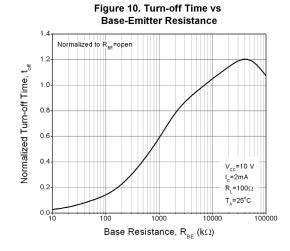


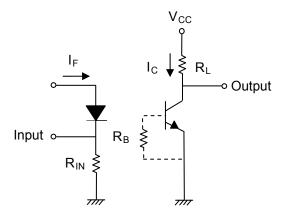
Figure 8. Switching Time vs Load Resistance

Tolday Delignor Supplies to the second resistance of the second resistance, R, (k\Omega)

Figure 9. Turn-on Time vs Base-Emitter Resistance)

3.0 Normalized to R_{BE} =open V_{Cc} =10 V_{Cc} =2mA R_{L} =100 Ω T_{A} =25°C T_{\text





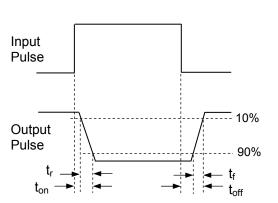


Figure 11. Switching Time Test Circuit & Waveforms



4N2X Series 4N3X Series H11AX Series

Order Information

Part Number

4NXXY(Z)-V or H11AXY(Z)-V

Note

XX = Part no. for 4NXX series (25, 26, 27, 28, 35, 36, 37 or 38)

X = Part no. for H11AX series (1, 2, 3, 4, or 5)

Y = Lead form option (S, S1, M or none)

Z = Tape and reel option (TA, TB or none).

V = VDE safety (optional)

Option	Description	Packing quantity
None	Standard DIP-6	65 units per tube
M	Wide lead bend (0.4 inch spacing)	65 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel

7

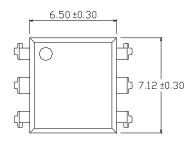


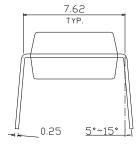
4N2X Series 4N3X Series H11AX Series

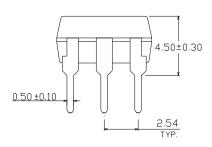
Package Drawings

(Dimensions in mm)

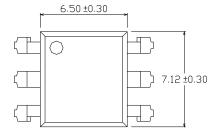
Standard DIP Type

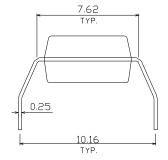


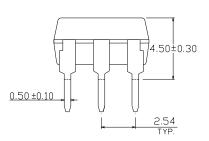




Option M Type



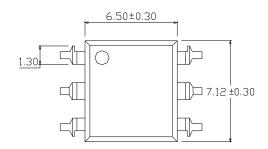


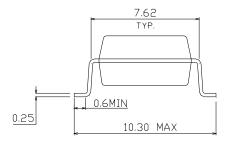


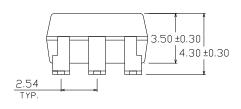


4N2X Series 4N3X Series H11AX Series

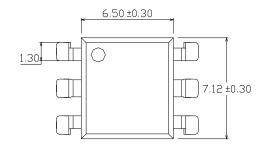
Option S Type

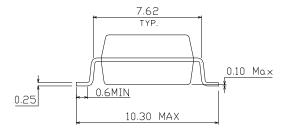


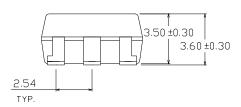




Option S1 Type



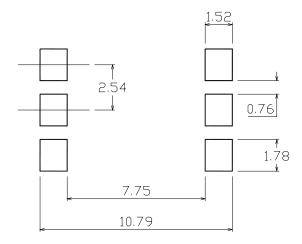




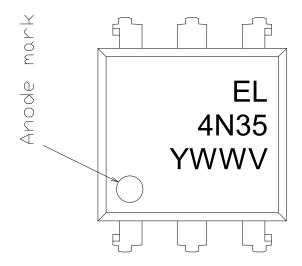


4N2X Series 4N3X Series H11AX Series

Recommended pad layout for surface mount leadform



Device Marking



Notes

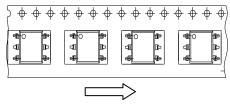
EL denotes Everlight
4N35 denotes Device Number
Y denotes 1 digit Year code
WW denotes 2 digit Week code
V denotes VDE (optional)



4N2X Series 4N3X Series H11AX Series

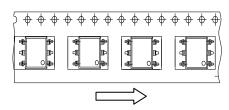
Tape & Reel Packing Specifications

Option TA



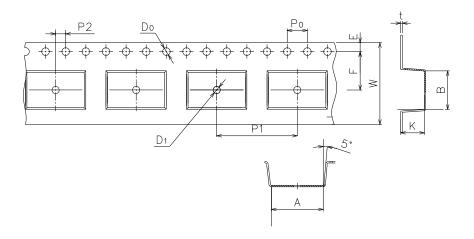
Direction of feed from reel

Option TB



Direction of feed from reel

Tape dimensions



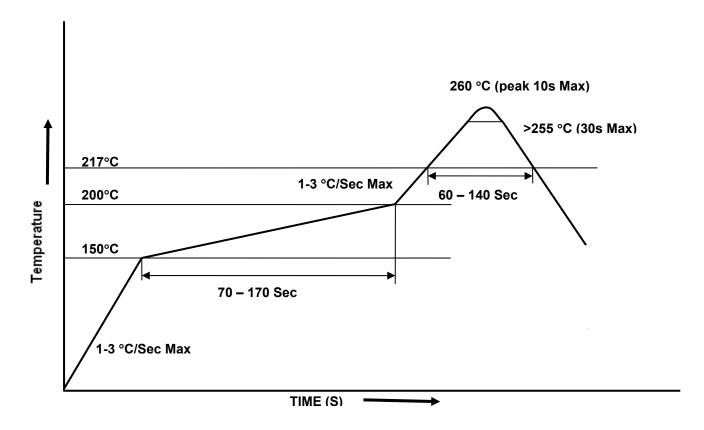
Dimension No.	Α	В	Do	D1	E	F
Dimension (mm)	10.4±0.1	7.52±0.1	1.5±0.1	1.5+0.1/-0	1.75±0.1	7.5±0.1

Dimension No.	Ро	P1	P2	t	w	К
Dimension (mm)	4.0±0.15	16.0±0.1	2.0±0.1	0.35±0.03	16.0±0.2	4.5±0.1



4N2X Series 4N3X Series H11AX Series

Solder Reflow Temperature Profile





4N2X Series 4N3X Series H11AX Series

DISCLAIMER

- 1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
- 2. When using this product, please observe the absolute maximum ratings and the instructions for use as outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
- 3. These specification sheets include materials protected under copyright of EVERLIGHT Corporation. Reproduction in any form is prohibited without the specific consent of EVERLIGHT.